

# **FMMT415TA Datasheet**



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DiGi Electronics Part Number FMMT415TA-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number FMMT415TA

Description TRANS NPN 100V 0.5A SOT23-3

**Detailed Description** Bipolar (BJT) Transistor NPN - Avalanche Mode 100

V 500 mA 40MHz 330 mW Surface Mount SOT-23-3



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FMMT415

8541.21.0095

## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
FMMT415TA	Diodes Incorporated
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN - Avalanche Mode	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
100 V	500mV @ 1mA, 10mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	25 @ 10mA, 10V
Power - Max:	Frequency - Transition:
330 mW	40MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	SOT-23-3
Base Product Number:	

## **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





#### **NPN AVALANCHE TRANSISTOR IN SOT23**

#### **Features**

- Avalanche Transistor
- 60A Peak Avalanche Current (Pulse width = 20ns)
- BV<sub>CES</sub> > 260V (415) & 320V (417)
- BV<sub>CEO</sub> > 100V
- Specifically designed for Avalanche mode operation
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### Description

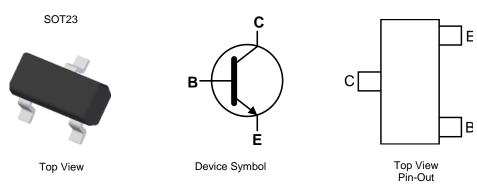
The FMMT415/417 are NPN silicon planar bipolar transistors designed for operating in avalanche mode. Tight process control and low inductance packaging combine to produce high-current pulses with fast edges.

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic. "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
  Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)

#### **Applications**

- Laser Diode Drivers for Ranging and Measurement (LIDAR)
- Radar Systems
- Fast Edge Switch Generator
- · High Speed Pulse Generators



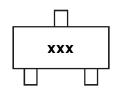
#### Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT415TD	AEC-Q101	415	7	8	500
FMMT417TD	AEC-Q101	417	7	8	500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



xxx = Product Type Marking Code (See Ordering Information)



## **Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	FMMT415	FMMT417	Unit
Collector-Base Voltage	V <sub>CBO</sub>	260	320	V
Collector-Emitter Voltage	V <sub>CES</sub>	260	320	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	6		V
Continuous Collector Current	Ic	500		mA
Peak Collector Current (Pulse Width = 20ns)	I <sub>CM</sub>	60		Α

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	$P_{D}$	500	mW
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	250	°C/W
Thermal Resistance, Junction to Lead	(Note 6)	$R_{ heta JL}$	197	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

#### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

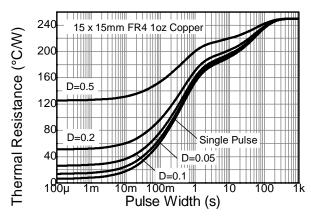
<sup>5.</sup> For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

<sup>6.</sup> Thermal resistance from junction to solder-point (at the end of the collector lead).

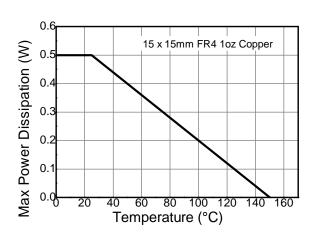
<sup>7.</sup> Refer to JEDEC specification JESD22-A114 and JESD22-A115.



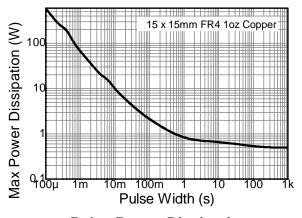
### **Thermal Characteristics and Derating Information**



**Transient Thermal Impedance** 



**Derating Curve** 



**Pulse Power Dissipation** 



### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

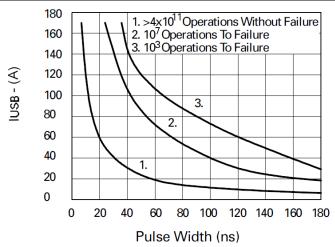
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Emitter Breakdown Voltage	FMMT415	BV <sub>CES</sub>	260	_	_	V	I <sub>C</sub> = 1mA T <sub>J</sub> = -55 to +150°C
	FMMT417		320	_			I <sub>C</sub> = 1mA
Collector-Emitter Breakdown Voltage (Not	e 8)	BV <sub>CEO</sub>	100	1	1	>	$I_C = 100\mu A$
Emitter-Base Breakdown Voltage		BV <sub>EBO</sub>	6	1	1	>	$I_E = 100\mu A$
Collector Cutoff Current		I <sub>CBO</sub>	_	ı	100 10	nA µA	V <sub>CB</sub> = 180V V <sub>CB</sub> = 180V, T <sub>J</sub> = +100°C
Emitter Cutoff Current		I <sub>EBO</sub>	_	1	100	nA	V <sub>EB</sub> = 4V
Static Forward Current Transfer Ratio (Note 8)		h <sub>FE</sub>	25	1	1	I	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V
Collector-Emitter Saturation Voltage (Note 8)		V <sub>CE(sat)</sub>	_	1	500	mV	$I_C = 10mA$ , $I_B = 1mA$
Base-Emitter Saturation Voltage (Note 8)		V <sub>BE(sat)</sub>	_		900	mV	$I_C = 10mA$ , $I_B = 1mA$
Pulsed Current in Second Breakdown		I <sub>USB</sub>	_	25 35	_	A A	$V_C = 200V, C_{CE} = 620pF$ $V_C = 250V, C_{CE} = 620pF$
Collector-Emitter Inductance		L <sub>ce</sub>	_	2.5	_	nΗ	Standard SOT23 leads
Output Capacitance		C <sub>obo</sub>	_	_	8	pF	$V_{CB} = 20V$ , $I_E = 0$ f = 100MHz
Transition Frequency		f <sub>T</sub>	40	-	-	MHz	$V_{CE} = 20V$ , $I_C = 10mA$ , $f = 20MHz$

Note:

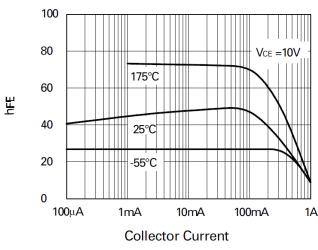
8. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



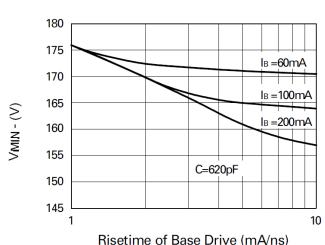
#### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



#### Maximum Avalanche Current v Pulse Width

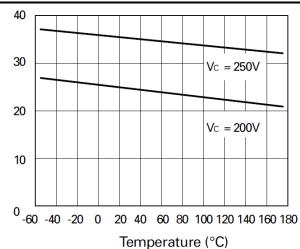


#### hfe v IC

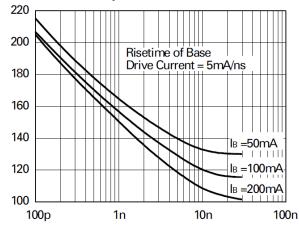


Minimum starting voltage

## Minimum starting voltage as a function of drive current

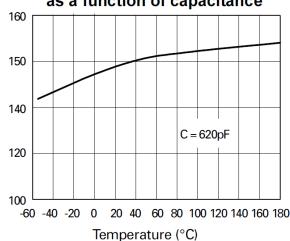


## **IUSB v Temperature** for the specified conditions



Collector-Emitter Capacitance (F)

# Minimum starting voltage as a function of capacitance

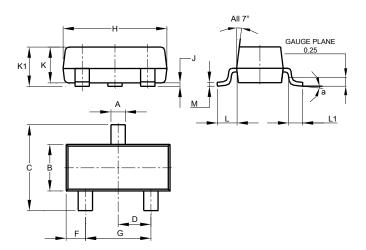


Minimum starting voltage as a function of temperature



## **Package Outline Dimensions**

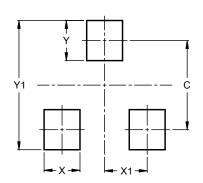
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Υ	0.9
Y1	2.9

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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